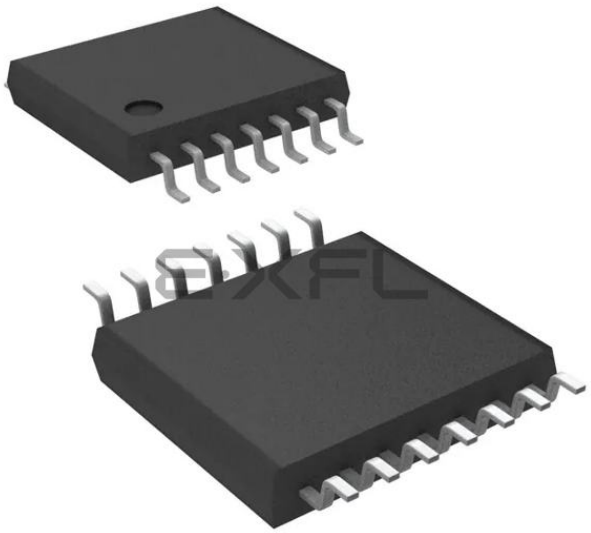

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	11
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	14-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	14-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l011d3p6tr

Contents

1 Introduction

The ultra-low-power STM32L011x3/4 family includes devices in 7 different package types from 14 to 32 pins. The description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L011x3/4 microcontrollers suitable for a wide range of applications:

- Gas/water meters and industrial sensors
- Healthcare and fitness equipment
- Remote control and user interface
- PC peripherals, gaming, GPS equipment
- Alarm system, wired and wireless sensors, video intercom

This STM32L011x3/4 datasheet should be read in conjunction with the STM32L0x1 reference manual (RM0377).

For information on the ARM® Cortex®-M0+ core please refer to the Cortex®-M0+ Technical Reference Manual, available from the www.arm.com website.

Figure 1 shows the general block diagram of the device family.

3 Functional overview

3.1 Low-power modes

The ultra-low-power STM32L011x3/4 supports dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

- **Low-power run mode**

  This mode is achieved with the multispeed internal (MSI) RC oscillator set to the low-speed clock (max 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Low-power run mode, the clock frequency and the number of enabled peripherals are both limited.

- **Low-power sleep mode**

  This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

  When wakeup is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

- **Stop mode with RTC**

  The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSE and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

  Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

  The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event

(if internal reference voltage is on), it can be the RTC alarm/tamper/timestamp/wakeup events, the USART/I2C/LPUART/LPTIM wakeup events.

- **Stop mode without RTC**

  The Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillator are disabled.

  Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

  The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 3.5 µs, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event (if internal reference voltage is on). It can also be wakened by the USART/I2C/LPUART/LPTIM wakeup events.

- **Standby mode with RTC**

  The Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSE bypass and HSI RC oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

  The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby mode without RTC**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillator are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32 KHz oscillator, RCC_CSR register).

  The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 3. Functionalities depending on the operating power supply range

Operating power supply range	Functionalities depending on the operating power supply range		
	ADC operation	Dynamic voltage scaling range	I/O operation
V_{DD} = 1.65 to 1.71 V	ADC only, conversion time up to 570 ksps	Range 2 or range 3	Degraded speed performance
V_{DD} = 1.71 to 1.8 V(1)	ADC only, conversion time up to 1.14 Msps	Range 1, range 2 or range 3	Degraded speed performance

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L011x3/4 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.4 Reset and supply management

3.4.1 Power supply schemes

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively. On TSSOP14 package, V_{DDA} is internally connected to V_{DD}.

3.4.2 Power supply supervisor

The devices feature an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

The BOOT0 pin is shared with PB9 GPIO pin. This pin is an input-only pin. If nBOOT_SEL option bit is reset, sampling this pin on NRST rising edge gives the internal BOOT0 state. This pin then works as PB9 pin. The input voltage characteristics of this pin are specific for BOOT0 pin type (see *Table 50: I/O static characteristics*).

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event

(rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 38 GPIOs can be connected to the 16 configurable interrupt/event lines. The 10 other lines are connected to PVD, RTC, USART, I2C, LPUART, LPTIM or comparator events.

3.8 Memories

The STM32L011x3/4 devices have the following features:

- 2 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 8 or 16 Kbytes of embedded Flash program memory
  - 512 bytes of data EEPROM
  - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- **Level 0**: no protection
- **Level 1**: memory readout protected.

  The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2**: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Direct memory access (DMA)

The flexible 5-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C, USART, LPUART, general-purpose timers, and ADC.

3.17 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Table 14. Alternate functions (continued)

Ports		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SPI1/USART2/ TIM21/ EVENTOUT/ SYS_AF	SPI1/I2C1/ LPTIM	LPUART1/ LPTIM/TIM2/ EVENTOUT/ SYS_AF	I2C1/LPTIM/ EVENTOUT	I2C1/USART2/LPUART1/ EVENTOUT	SPI1/TIM2/21	LPUART1/EVEVENTOUT	COMP1/2
Port B	PB0	EVENTOUT	SPI1_MISO	TIM2_CH2	-	USART2_RTS	TIM2_CH3	-	-
	PB1	USART2_CK	SPI1_MOSI	LPTIM1_IN1	-	LPUART1_RTS	TIM2_CH4	-	-
	PB2	-	-	LPTIM1_OUT	-	-	-	-	-
	PB3	SPI1_SCK	-	TIM2_CH2	-	EVENTOUT	-	-	-
	PB4	SPI1_MISO	-	EVENTOUT	-	-	-	-	-
	PB5	SPI1_MOSI	-	LPTIM1_IN1	I2C1_SMBA	-	TIM21_CH1	-	-
	PB6	USART2_TX	I2C1_SCL	LPTIM1_ETR	-	-	TIM2_CH3	LPUART1_TX	-
	PB7	USART2_RX	I2C1_SDA	LPTIM1_IN2	-	-	TIM2_CH4	LPUART1_RX	-
	PB8	USART2_TX	-	EVENTOUT	-	I2C1_SCL	SPI1_NSS	-	-
	PB9	-	-	-	-	-	-	-	-
Port C	PC14	-	-	-	-	-	-	-	-
	PC15	-	-	-	-	-	-	-	-

Table 16. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD} (2)	Total current into sum of all V_{DD} power lines (source)(1)	105	mA
ΣI_{VSS} (2)	Total current out of sum of all V_{SS} ground lines (sink)(1)	105	
$I_{VDD(PIN)}$	Maximum current into each V_{DD} power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each V_{SS} ground pin (sink)(1)	100	
I_{IO}	Output current sunk by any I/O and control pin except FTf pins	16	
	Output current sunk by FTf pins	22	
	Output current sourced by any I/O and control pin	-16	
$\Sigma I_{IO(PIN)}$ (3)	Total output current sunk by sum of all IOs and control pins(4)	45	
	Total output current sourced by sum of all IOs and control pins	-45	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	90	
	Total output current sourced by sum of all IOs and control pins(2)	-90	
$I_{INJ(PIN)}$	Injected current on FT, FFf, RST and B pins	-5/+0(5)	
	Injected current on TC pin	± 5(6)	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(7)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. These values apply only to STM32L011GxUx part number (UFQFPN28 package).
4. This current consumption must be correctly distributed over all I/Os and control pins. In particular, it must be located the closest possible to the couple of supply and ground, and distributed on both sides.
5. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15* for maximum allowed input voltage values.
6. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 15: Voltage characteristics* for the maximum allowed input voltage values.
7. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 17. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 26. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	36.5	70	µA
				2 MHz	58	95	
				4 MHz	100	150	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	125	170	
				8 MHz	230	300	
				16 MHz	450	540	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	275	350	
				16 MHz	555	650	
				32 MHz	1350	1600	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	15.5	32	
				524 kHz	26.5	55	
				4.2 MHz	115	160	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	585	670	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	49	88	
				2 MHz	69	120	
				4 MHz	115	190	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	135	200	
				8 MHz	240	340	
				16 MHz	460	650	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	290	400	
				16 MHz	565	750	
				32 MHz	1350	1900	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	26.5	46	
				524 kHz	38.5	70	
				4.2 MHz	125	190	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	600	760	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1500	1850	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Figure 17. I_{DD} vs V_{DD}, at T_A= -40/25/55/ 85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS

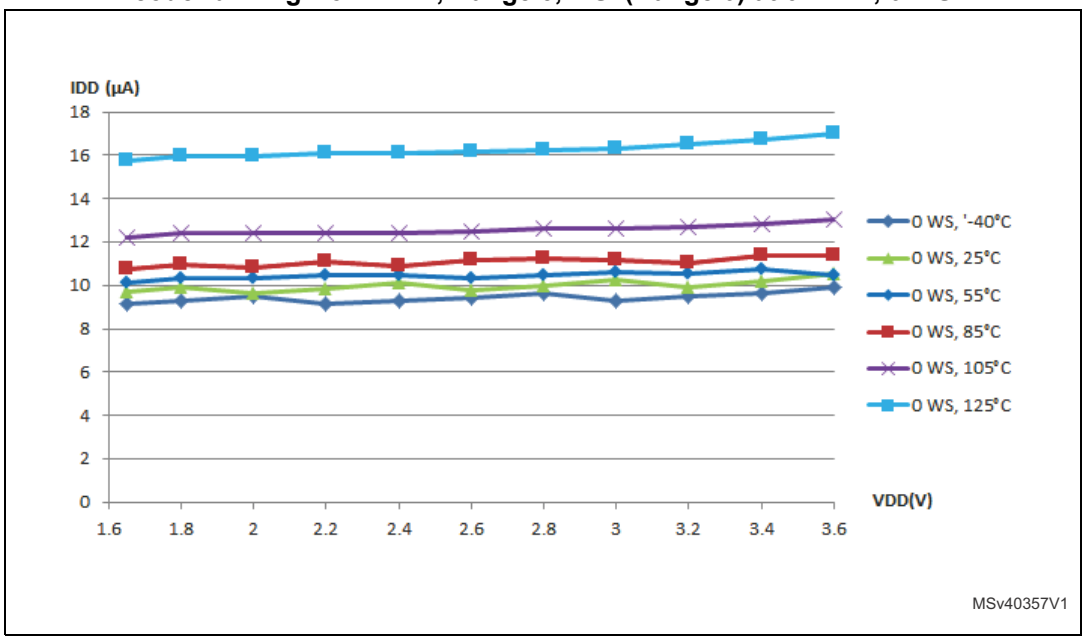


Table 28. Current consumption in Low-power Sleep mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
I_{DD} (LP Sleep)	Supply current in Low-power sleep mode	All peripherals OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash OFF	T_A = -40 °C to 25 °C	2.5(2)	-	µA
			MSI clock, 65 kHz f_{HCLK} = 32 kHz Flash ON	T_A = -40 °C to 25 °C	13	19	
				T_A = 85 °C	15.5	20	
				T_A = 105 °C	17.5	22	
				T_A = 125 °C	21	29	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz, Flash ON	T_A = -40 °C to 25 °C	13.5	19	
				T_A = 85 °C	16	20	
				T_A = 105 °C	18	22	
				T_A = 125 °C	21.5	29	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz, Flash ON	T_A = -40 °C to 25 °C	15.5	21	
				T_A = 55 °C	17	22	
				T_A = 85 °C	18	23	
				T_A = 105 °C	19.5	24	
				T_A = 125 °C	23.5	31	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.
2. As the CPU is in Sleep mode, the difference between the current consumption with Flash memory ON and OFF (nearly 12 µA) is the same whatever the clock frequency.

Table 30. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Standby)	Supply current in Standby mode	Independent watchdog and LSI enabled	T_A = -40 °C to 25 °C	0.8	1.6	µA
			T_A = 55 °C	0.9	1.8	
			T_A= 85 °C	1	2	
			T_A = 105 °C	1.25	3	
			T_A = 125 °C	2	7	
		Independent watchdog and LSI OFF	T_A = -40 °C to 25 °C	0.23	0.6	
			T_A = 55 °C	0.25	0.7	
			T_A = 85 °C	0.36	1	
			T_A = 105 °C	0.62	1.7	
			T_A = 125 °C	1.35	5	

1. Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified

Table 31. Average current consumption during wakeup

Symbol	parameter	System frequency	Current consumption during wakeup	Unit
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	HSI	1	mA
		HSI/4	0,7	
		MSI 4,2 MHz	0,7	
		MSI 1,05 MHz	0,4	
		MSI 65 KHz	0,1	
I_{DD} (Reset)	Reset pin pulled down	-	0,21	
I_{DD} (Power Up)	BOR ON	-	0,23	
I_{DD} (WU from StandBy)	With Fast wakeup set	MSI 2,1 MHz	0,5	
	With Fast wakeup disabled	MSI 2,1 MHz	0,12	

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked OFF
  - with only one peripheral clocked ON

Table 32. Peripheral current consumption in run or Sleep mode(1)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	Low-power sleep and run	
APB1	WWDG	2.5	2	1.6	2	µA/MHz (f_{HCLK})
	LPUART1	8.3	7.2	5.4	7.2	
	I2C1	11	8.2	6.8	8.9	
	LPTIM1	14	11	8.7	11	
	TIM2	10.5	8.5	6.4	8.5	
	USART2	8.5	6.8	5.4	7.1	
APB2	ADC1(2)	5.0	3.9	3.3	4	µA/MHz (f_{HCLK})
	SPI1	4.5	3.5	2.9	3.6	
	TIM21	6.8	6.1	4.5	5.6	
	DBGMCU	1.7	1.7	1.1	1.4	
	SYSCFG/ COMP	2.5	2.4	1.6	2.3	
Cortex-M0+ core I/O port	GPIOA	7.6	6.3	4.9	6.5	µA/MHz (f_{HCLK})
	GPIOB	5.1	4.1	3.2	4	
	GPIOC	1.1	0.7	0.6	0.8	
AHB	CRC	1.5	1.1	1	1.2	µA/MHz (f_{HCLK})
	FLASH(3)	10	8.5	7	8.5	
	DMA1	5.3	4.2	3.5	4.8	
All enabled		96	80	62	88	
PWR		2.1	1.9	1.4	1.8	µA/MHz (f_{HCLK})

1. Data based on differential I_{DD} measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f_{HCLK} = 32 MHz (range 1), f_{HCLK} = 16 MHz (range 2), f_{HCLK} = 4 MHz (range 3), f_{HCLK} = 64kHz (Low-power run/sleep), $f_{APB1} = f_{HCLK}$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling. Not tested in production.
2. HSI oscillator is OFF for this measure.
3. These values correspond to the Flash memory dynamic current consumption. The Flash memory static consumption (Flash memory ON) equals 12 µA and does not depend on the frequency.
The Flash memory consumption is already taken into account in all the supply current consumption tables (Flash memory ON cases).

Table 40. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{SU(MSI)}$	MSI oscillator startup time	MSI range 0	30	-	µs
		MSI range 1	20	-	
		MSI range 2	15	-	
		MSI range 3	10	-	
		MSI range 4	6	-	
		MSI range 5	5	-	
		MSI range 6, Voltage range 1 and 2	3.5	-	
		MSI range 6, Voltage range 3	5	-	
$t_{STAB(MSI)}$(2)	MSI oscillator stabilization time	MSI range 0	-	40	µs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results, not tested in production.

6.3.8 PLL characteristics

The parameters given in *Table 41* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 18*.

Table 41. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max(1)	
f_{PLL_IN}	PLL input clock(2)	2	-	24	MHz
	PLL input clock duty cycle	45	-	55	%

Table 41. PLL characteristics (continued)

Symbol	Parameter	Value			Unit
		Min	Typ	Max(1)	
f_{PLL_OUT}	PLL output clock	2	-	32	MHz
t_{LOCK}	PLL input = 16 MHz PLL VCO = 96 MHz	-	115	160	µs
Jitter	Cycle-to-cycle jitter	-		±600	ps
I_{DDA}(PLL)	Current consumption on V_{DDA}	-	220	450	µA
I_{DD}(PLL)	Current consumption on V_{DD}	-	120	150	

1. Guaranteed by characterization results, not tested in production.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT}.

6.3.9 Memory characteristics

RAM memory

Table 42. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode(1)	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 26* and *Table 52*, respectively.

Unless otherwise specified, the parameters given in *Table 52* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 18*.

Table 52. I/O AC characteristics(1)(2)

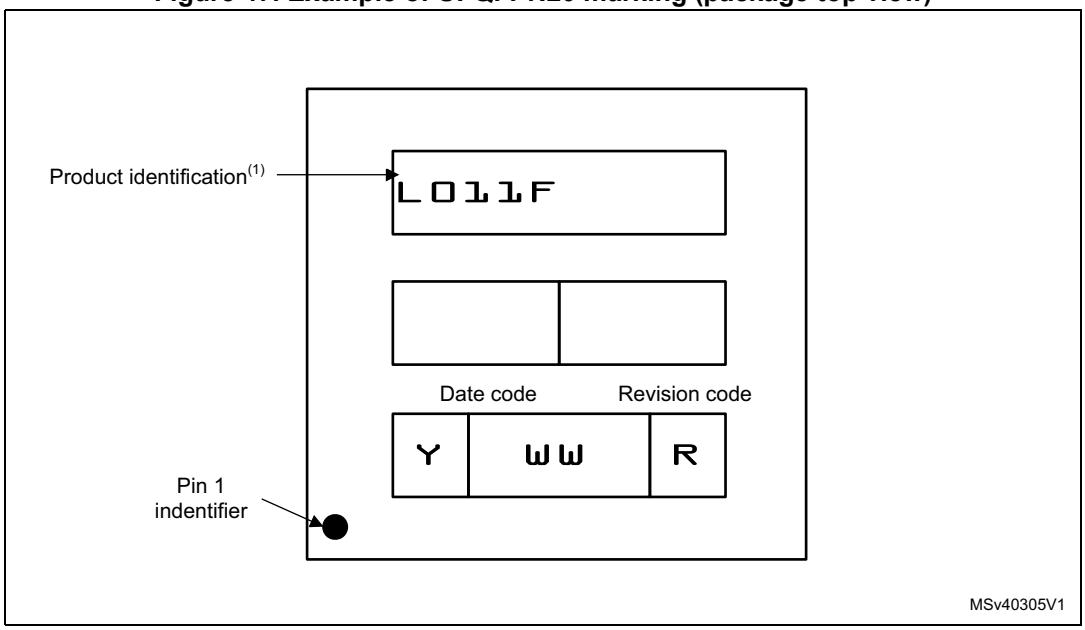
OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(3)	Unit
00	$f_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	100	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	320	
01	$f_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	0.6	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	30	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	65	
10	$F_{max(IO)out}$	Maximum frequency(4)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	13	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	28	
11	$F_{max(IO)out}$	Maximum frequency(4)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	35	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	10	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	6	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	17	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the line reference manual for a description of GPIO Port configuration register.
2. BOOT0/PB9 maximum input frequency is 10 kHz (1.65 V < V_{DD} < 2.7 V) and 5 MHz (2.7 V < V_{DD} < 3.6 V).
3. Guaranteed by design. Not tested in production.
4. The maximum frequency is defined in *Figure 26*.

UFQFPN20 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

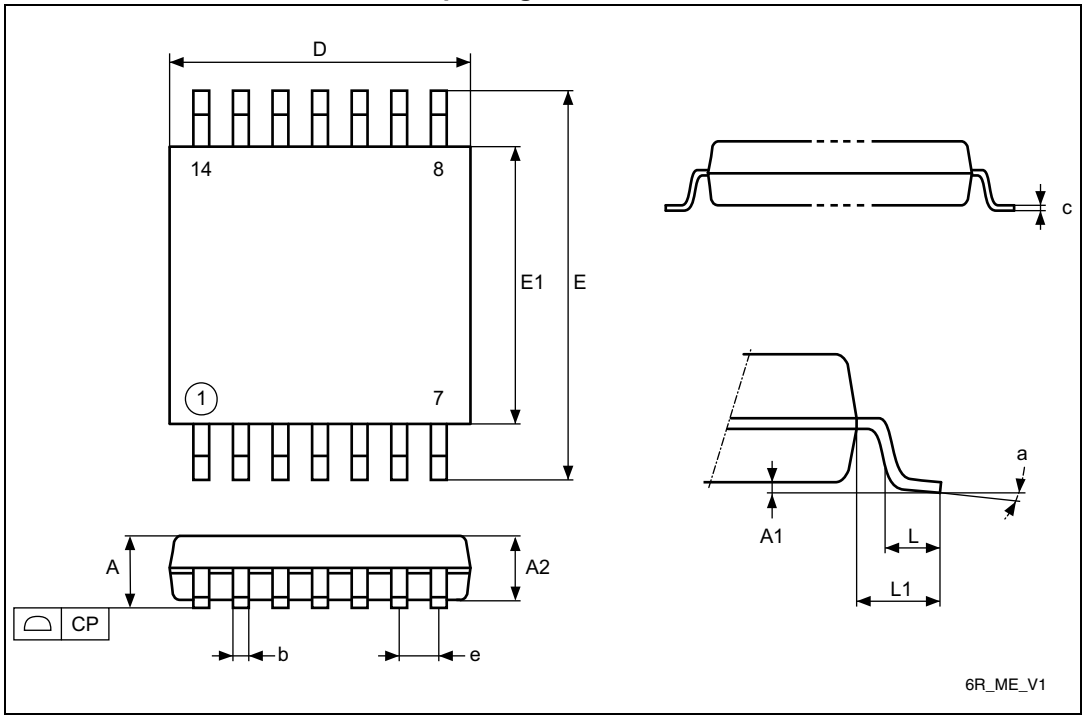
Figure 47. Example of UFQFPN20 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.7 TSSOP14 package information

Figure 51.TSSOP14 – 14-lead thin shrink small outline, 5.0 x 4.4 mm, 0.65 mm pitch, package outline



1. Drawing is not to scale.

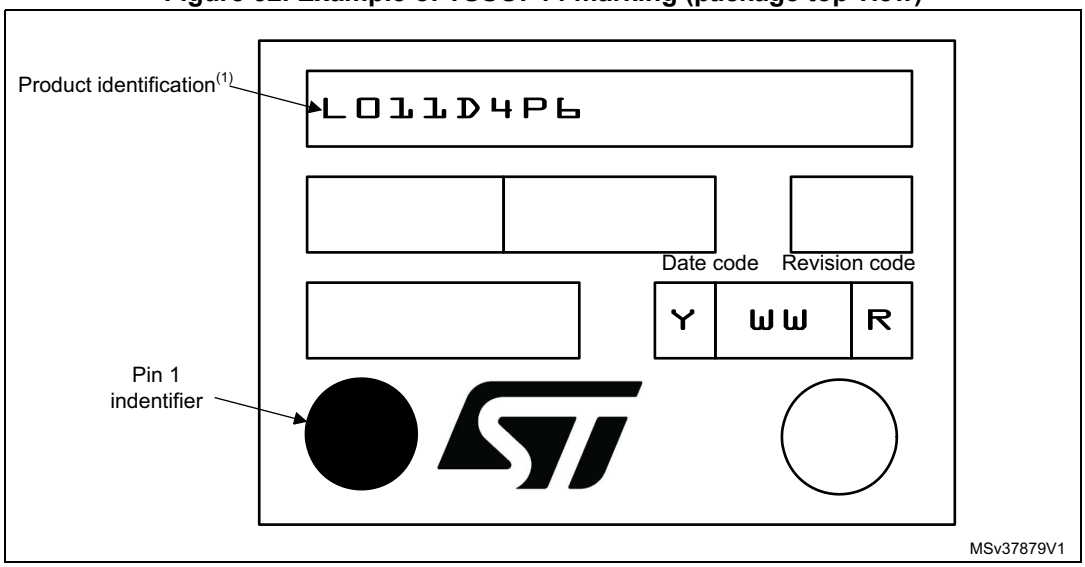
Table 75. TSSOP14 – 14-lead thin shrink small outline, 5.0 x 4.4 mm, 0.65 mm pitch, package mechanical data

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
CP	-	-	0.100	-	-	0.0039
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
e	-	0.650	-	-	0.0256	-
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1	4.300	4.400	4.500	0.1693	0.1732	0.1772
L	0.500	0.600	0.750	0.0197	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
a	0°	-	8°	0°	-	8°

TSSOP14 device marking

The following figure gives an example of topside marking versus pin 1 position identifier location.

Figure 52. Example of TSSOP14 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.8 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max × Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.